Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

1. (Cancelled)

2. (Currently Amended) [[The]] A semiconductor device ~~according to claim 1, wherein~~ comprising a boosting circuit that supplies a power supply voltage during a standby state of the semiconductor device, the boosting circuit including:

a charge pump circuit;

a first detection circuit that detects an output voltage of the charge pump circuit; and

a second detection circuit that detects the output voltage of the charge pump circuit, the second detection circuit operating with a DC current greater than that of the first detection circuit and being activated by a detection signal of the first detection circuit,

wherein the charge pump circuit is activated based on at least a detection signal of the second detection circuit, and

the detection level of the second detection circuit is higher than the detection level of the first detection circuit.

3. (Currently Amended) [[The]] A semiconductor device ~~according to claim 1, wherein~~ comprising a boosting circuit that supplies a power supply voltage during a standby state of the semiconductor device, the boosting circuit including:

a charge pump circuit;

a first detection circuit that detects an output voltage of the charge pump circuit; and

a second detection circuit that detects the output voltage of the charge pump circuit, the second detection circuit operating with a DC current greater than that of the first detection circuit and being activated by a detection signal of the first detection circuit,

wherein the charge pump circuit is activated based on at least a detection signal of the second detection circuit, and

the charge pump circuit is activated based on a result of AND operation of the detection signals of the first and second detection circuits.

4. (Currently Amended) The semiconductor device according to claim 2 ~~claim 1~~, wherein the second detection circuit generates a signal to inactivate the charge pump circuit based on a status in which the output voltage of the charge pump circuit reaches a predetermined voltage corresponding to the detection level of the second detection circuit.

5. (Currently Amended) The semiconductor device according to claim 2 ~~claim 1~~, wherein a period for which the second detection circuit is active is shorter than a period for which the first detection circuit is active.

6. (New) The semiconductor device according to claim 3, wherein the second detection circuit generates a signal to inactivate the charge pump circuit based on a status in which the output voltage of the charge pump circuit reaches a predetermined voltage corresponding to the detection level of the second detection circuit.

7. (New) The semiconductor device according to claim 3, wherein a period for which the second detection circuit is active is shorter than a period for which the first detection circuit is active.

8. (New) A semiconductor device comprising a boosting circuit for generating a power for the semiconductor device, the boosting circuit including:

a charge pump circuit;

a first detection circuit for detecting that an output voltage of the charge pump circuit reaches a first voltage and in response varying a level of its output signal; and

a second detection circuit for detecting that the output voltage of the charge pump circuit reaches a second voltage which is higher than the first voltage and in response varying a level of its output signal, the second detection circuit being activated by the output signal of the first detection circuit or the output signal of the second detection signal,

wherein the charge pump circuit is activated based on the output signal of the second detection circuit.